SPECIFICATION OF LED CHIP
C1650-30
[NIR]

1) Commodity Type and Physical Characteristics.

1. Material		InGaAsP/InP(DDH)	
2. Electrode	Top Side	P (anode) side	: Au Alloy
	Bottom Side	N (cathode) side	: Au Alloy
3. Electrode Pattern			Fig.1
4. Chip Size			Fig.2
5. Chip Thickness			Fig.2
6. Emission Area			Fig.2

2) Electro-Optical Characteristics

parameters		symbol	condition	min.	typ.	max.	unit
Forward Voltage		Vf	If=20mA		0.78	1.2	V
			If=50mA		0.85	1.3	
Reverse Current		Ir	Vr=3V			10	uA
Power Intensity		Po	If=20mA		0.75		mW
			If=50mA		1.50		
Wavelength	peac	λP	If=50mA	1600	1650	1700	nm
	centroid	λC			1615		
Spectral Radiation Bandwidth		Δλ	If=50mA		130		nm
RiseTime		tr	If=20mA		40		ns
FallTime		tf	If=20mA		40		ns

‡ Die shall be mounted on TO=18 gold header without resin coated. (Ta=25°C)

[Unit: um]

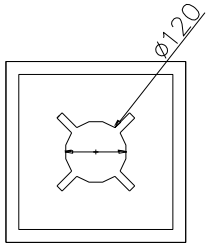

Fig.1 Electrode Pattern

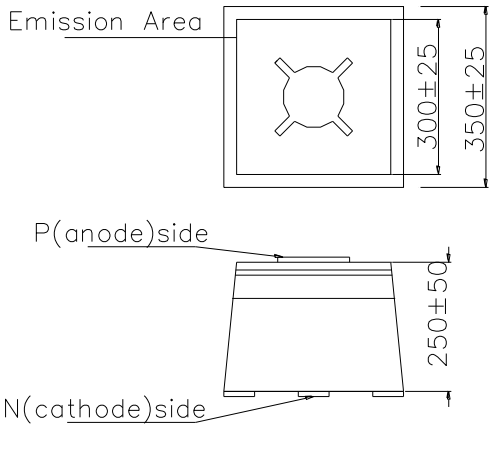

Fig.2 Chip size and Emission Area

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